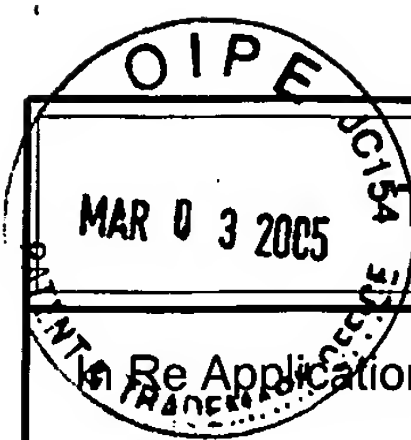


DFW



TRANSMITTAL OF FORMAL DRAWINGS

Docket No.
YOR920030203US1 (16694)

Re Application Of: Stephen W. Bedell, et al.

Application No.	Filing Date	Confirmation No.	Examiner	Customer No.	Group Art Unit
10/662,028	September 12, 2003	9297	Unassigned	23389	3661


Invention: **FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER**

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

7 sheets of formal drawing(s) for this application.

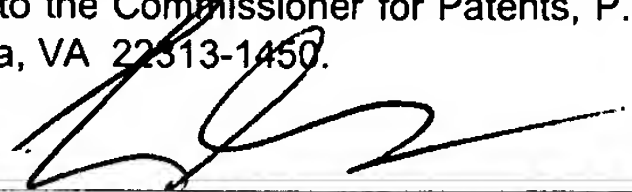
☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).


Signature

Leslie S. Szivos, Ph.D.
Registration No. 39,394

Dated: March 1, 2005

I certify that this document and attached formal drawings are being deposited on 03/01/05 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.



Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

Typed or Printed Name of Person Mailing Correspondence